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Form 1449*

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT
(Use several sheets if necessary)

Atty. Docket No.: 303.389US2

Serial No. Unknown

Applicant: Leonard Forbes et al.

Filing Date: Herewith

Group: Unknown

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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
EL	5,821,796	10/13/1998	Yaklin, D., et al.	327	313	09/23/96
EL	5,852,375	12/22/1998	Byrne, T.G., et al.	327	108	02/07/97
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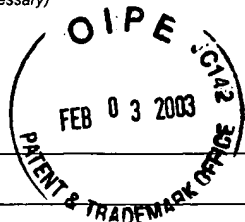
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)



Complete if Known

Application Number	09/467992
Filing Date	December 20, 1999
First Named Inventor	Forbes, Leonard
Group Art Unit	2815
Examiner Name	Lee, Eugene

Sheet 1 of 1

Attorney Docket No: 303.389US2

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
CL	US-6,238,976	05/29/2001	Noble, W. P., et al	438	259	02/27/1998

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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